

Silicon PNP Power Transistors

2SB945

DESCRIPTION

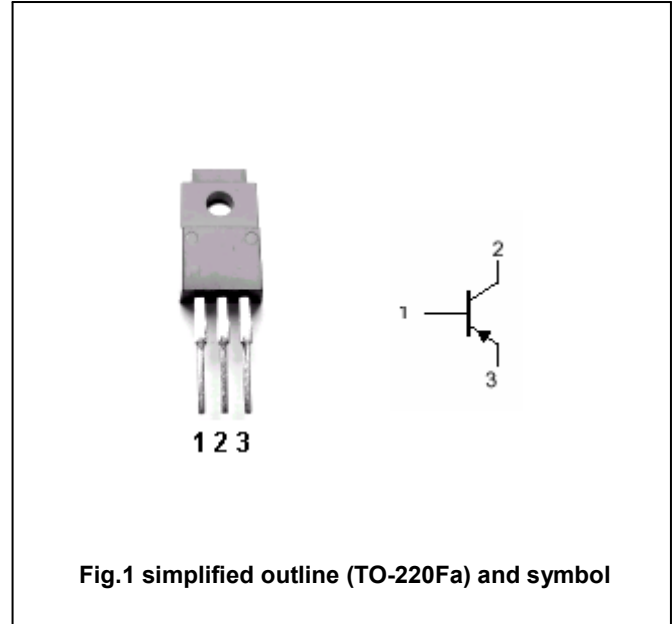
- With TO-220Fa package
- Large collector current I_C
- Low collector saturation voltage
- Complement to type 2SD1270

APPLICATIONS

- For power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-130	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-5	A
I_{CM}	Collector current-peak		-10	A
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	2	W
		$T_C=25^\circ\text{C}$	40	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA, I _B =0	-80			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-4A, I _B =-0.2A			-0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-4A, I _B =-0.2A			-1.5	V
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-50	μA
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-10	μA
h _{FE-1}	DC current gain	I _C =-0.1A; V _{CE} =-2V	45			
h _{FE-2}	DC current gain	I _C =-2A; V _{CE} =-2V	90		260	
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-10V, f=10MHz		30		MHz

Switching times

t _{on}	Turn-on time	I _C =-2A; I _{B1} =-0.2A, I _{B2} =0.2A		0.13		μs
t _{stg}	Storage time			0.5		μs
t _f	Fall time			0.13		μs

◆ h_{FE-2} Classifications

Q	P
90-180	130-260

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PACKAGE OUTLINE

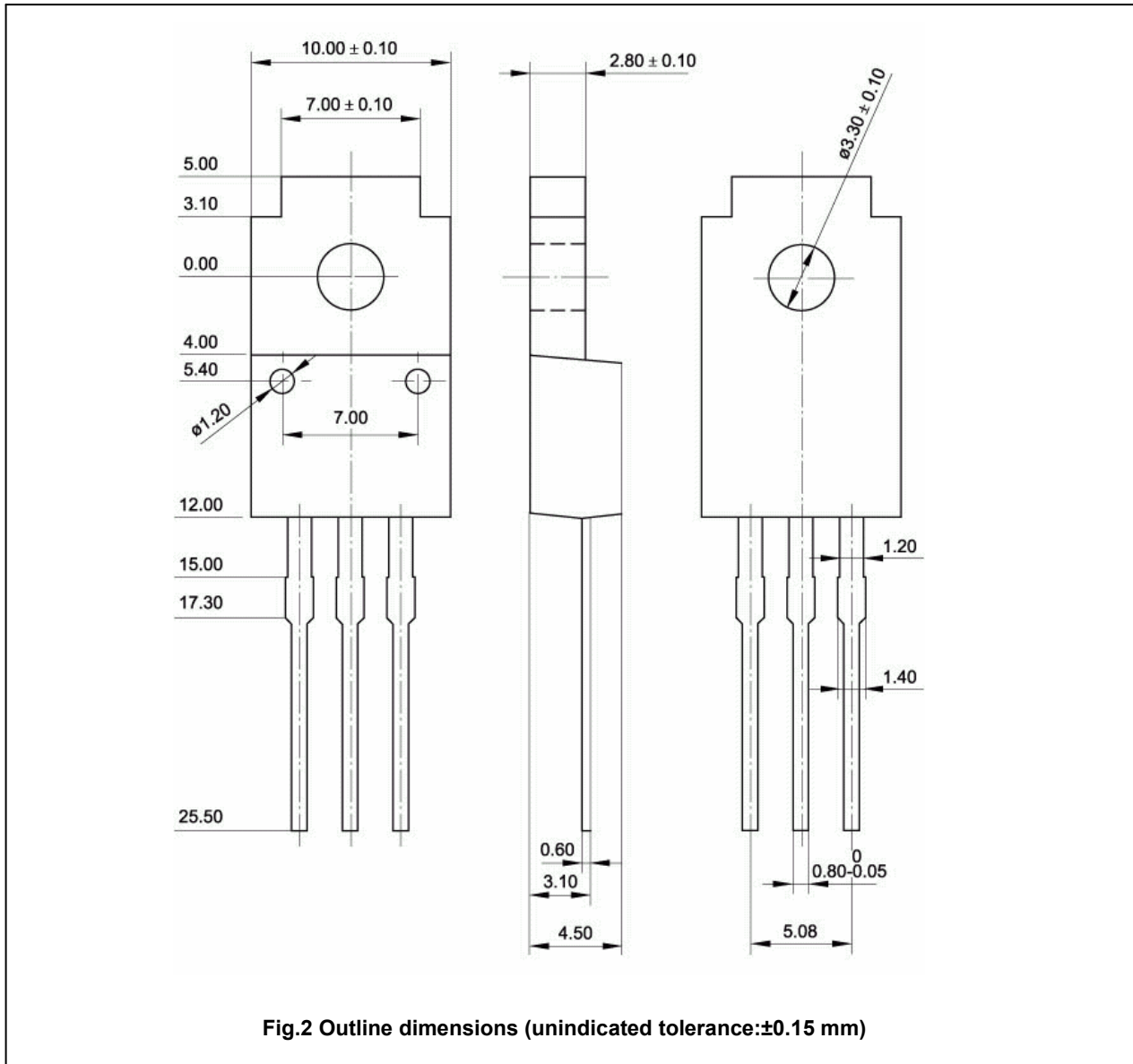


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)

